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FDD86113LZ

N-Channel Shielded Gate PowerTrench[®] MOSFET

100 V, 5.5 A, 104 mΩ

Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)}$ = 104 mΩ at $V_{GS} = 10$ V, $I_D = 4.2$ A
- Max $r_{DS(on)}$ = 156 mΩ at $V_{GS} = 4.5$ V, $I_D = 3.4$ A
- HBM ESD protection level > 6 kV typical (Note 4)
- High performance trench technology for extremely low $r_{DS(on)}$
- High power and current handling capability in a widely used surface mount package
- 100% UIL Tested
- RoHS Compliant

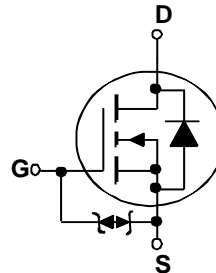
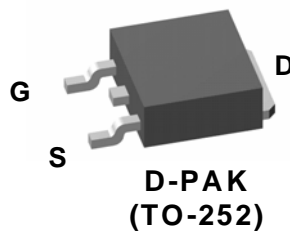


General Description

This N-Channel logic Level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench[®] process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and yet maintain superior switching performance. G-S zener has been added to enhance ESD voltage level.

Application

- DC-DC conversion



MOSFET Maximum Ratings $T_C = 25$ °C unless otherwise noted

| Symbol | Parameter | Rated | Units |
|----------------|--|-------------|-------|
| V_{DS} | Drain to Source Voltage | 100 | V |
| V_{GS} | Gate to Source Voltage | ± 20 | V |
| I_D | Drain Current -Continuous $T_C = 25$ °C | 5.5 | A |
| | -Continuous $T_A = 25$ °C (Note 1a) | 4.2 | |
| | -Pulsed | 15 | |
| E_{AS} | Single Pulse Avalanche Energy (Note 3) | 12 | mJ |
| P_D | Power Dissipation $T_C = 25$ °C | 29 | W |
| | Power Dissipation $T_A = 25$ °C (Note 1a) | 3.1 | |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

Thermal Characteristics

| | | | |
|-----------------|---|-----|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case (Note 1) | 4.3 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 96 | |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|------------|---------------|-----------|------------|------------|
| FDD86113LZ | FDD86113LZ | D-PAK(TO-252) | 13 " | 16 mm | 2500 units |

FDD86113LZ N-Channel Shielded Gate PowerTrench[®] MOSFET

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|---|-----|----|----------|----------------------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $I_D = 250\text{ }\mu\text{A}, V_{GS} = 0\text{ V}$ | 100 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$ | | 72 | | mV/ $^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| I_{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | | | ± 10 | μA |

On Characteristics

| | | | | | | |
|--|--|---|---|-----|-----|----------------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$ | 1 | 1.5 | 3 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$ | | -5 | | mV/ $^\circ\text{C}$ |
| $r_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = 10\text{ V}, I_D = 4.2\text{ A}$ | | 87 | 104 | m Ω |
| | | $V_{GS} = 4.5\text{ V}, I_D = 3.4\text{ A}$ | | 116 | 156 | |
| | | $V_{GS} = 10\text{ V}, I_D = 4.2\text{ A}, T_J = 125\text{ }^\circ\text{C}$ | | 142 | 170 | |
| g_{FS} | Forward Transconductance | $V_{DS} = 5\text{ V}, I_D = 4.2\text{ A}$ | | 9 | | S |

Dynamic Characteristics

| | | | | | | |
|------------|------------------------------|---|--|-----|-----|----------|
| C_{iss} | Input Capacitance | $V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | | 213 | 285 | pF |
| C_{oss} | Output Capacitance | | | 55 | 75 | pF |
| C_{riss} | Reverse Transfer Capacitance | | | 2.4 | 5 | pF |
| R_g | Gate Resistance | | | 1.4 | | Ω |

Switching Characteristics

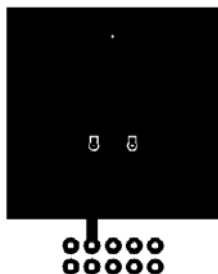
| | | | | | | |
|--------------|-------------------------------|---|---------------------------------------|-----|-----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 50\text{ V}, I_D = 4.2\text{ A}, V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$ | | 3.6 | 10 | ns |
| t_r | Rise Time | | | 1.3 | 10 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 9.7 | 20 | ns |
| t_f | Fall Time | | | 1.6 | 10 | ns |
| $Q_{g(TOT)}$ | Total Gate Charge | | $V_{GS} = 0\text{ V to } 10\text{ V}$ | | 3.7 | 6 |
| $Q_{g(TOT)}$ | Total Gate Charge | $V_{GS} = 0\text{ V to } 4.5\text{ V}$ | | 1.9 | 3 | |
| Q_{gs} | Gate to Source Charge | $V_{DD} = 50\text{ V}, I_D = 4.2\text{ A}$ | | 0.6 | | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | | 0.7 | | nC |

Drain-Source Diode Characteristics

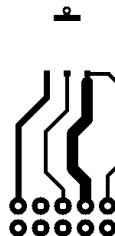
| | | | | | | |
|----------|---------------------------------------|--|--|------|-----|----|
| V_{SD} | Source to Drain Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_S = 4.2\text{ A}$ (Note 2) | | 0.88 | 1.3 | V |
| | | $V_{GS} = 0\text{ V}, I_S = 1.7\text{ A}$ (Note 2) | | 0.80 | 1.2 | |
| t_{rr} | Reverse Recovery Time | $I_F = 4.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | 31 | 49 | ns |
| Q_{rr} | Reverse Recovery Charge | | | 20 | 33 | nC |

NOTES:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 40 $^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b) 96 $^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

- Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0 %.
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 1\text{ mH}$, $I_{AS} = 5\text{ A}$, $V_{DD} = 90\text{ V}$, $V_{GS} = 10\text{ V}$.
- The diode connected between gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

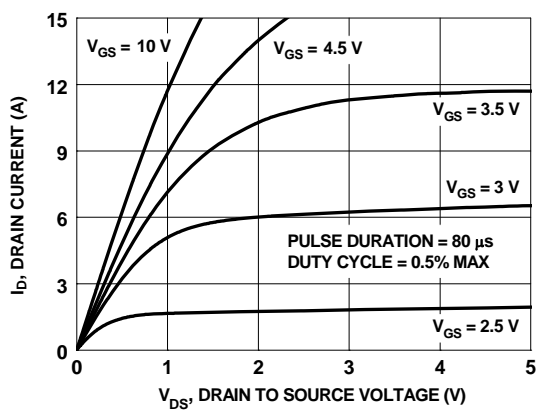


Figure 1. On-Region Characteristics

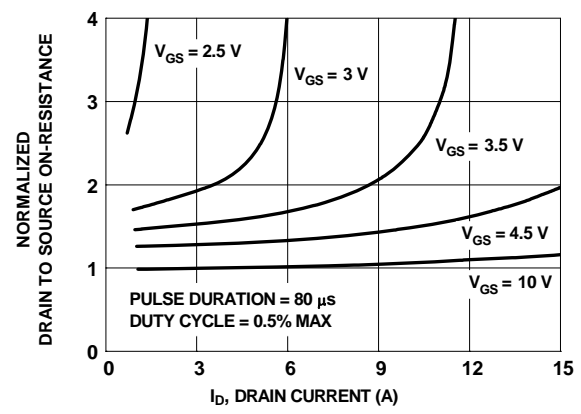


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

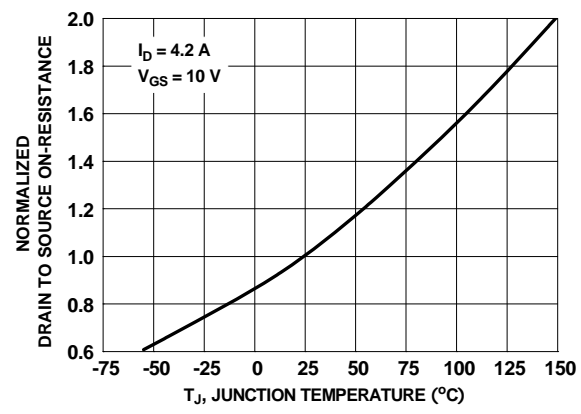


Figure 3. Normalized On-Resistance vs Junction Temperature

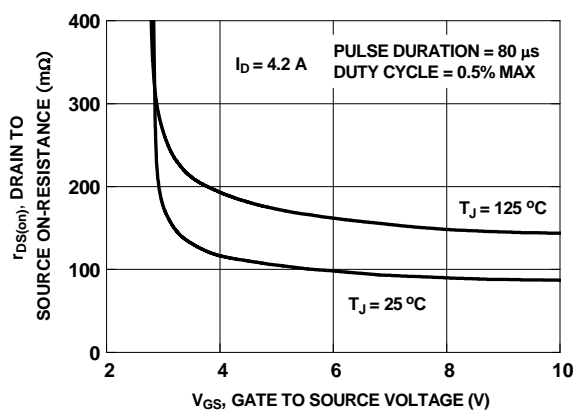


Figure 4. On-Resistance vs Gate to Source Voltage

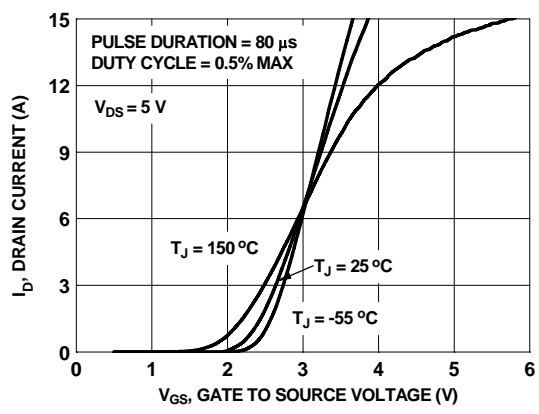


Figure 5. Transfer Characteristics

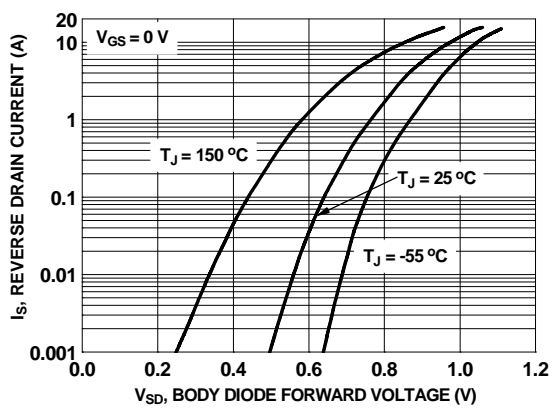


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

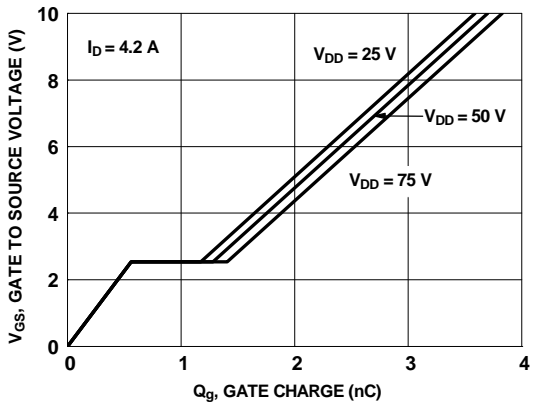


Figure 7. Gate Charge Characteristics

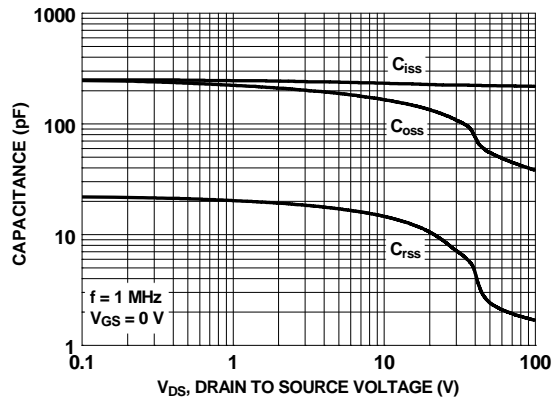


Figure 8. Capacitance vs Drain to Source Voltage

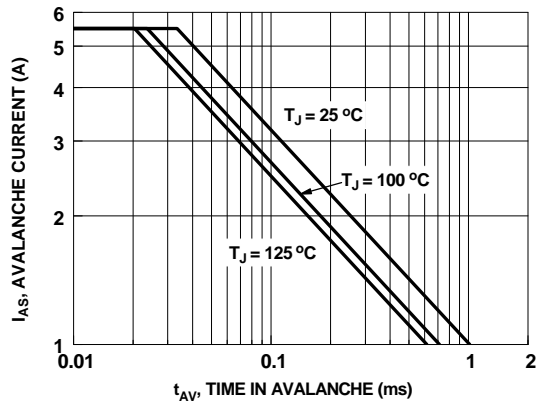


Figure 9. Unclamped Inductive Switching Capability

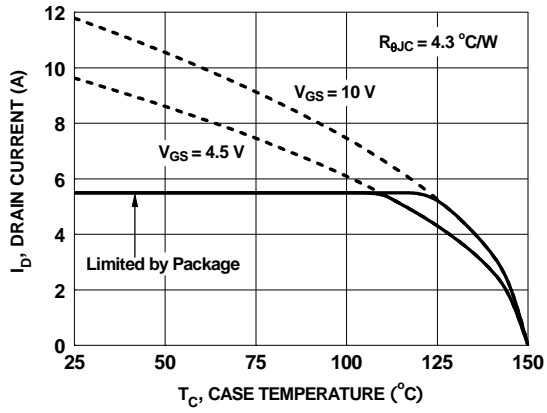


Figure 10. Maximum Continuous Drain Current vs Case Temperature

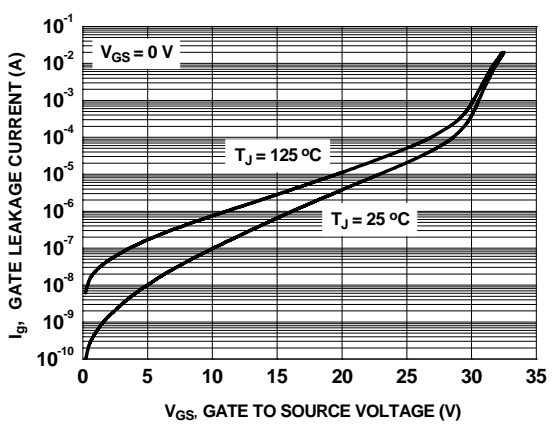


Figure 11. Gate Leakage Current vs Gate to Source Voltage

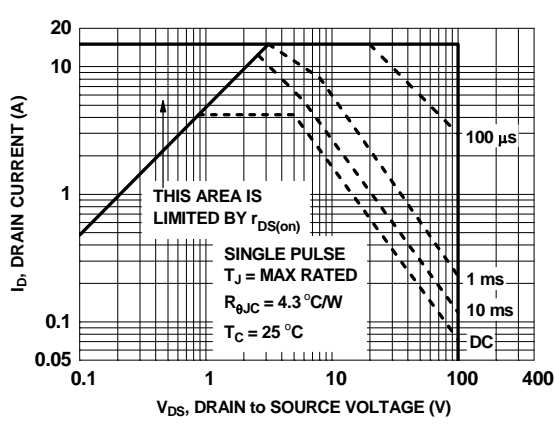


Figure 12. Forward Bias Safe Operating Area

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

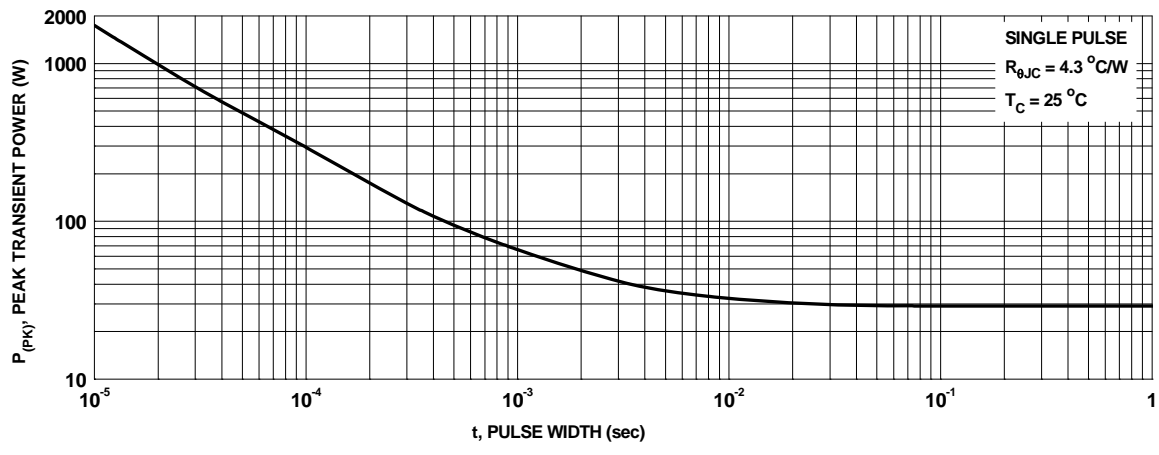


Figure 13. Single Pulse Maximum Power Dissipation

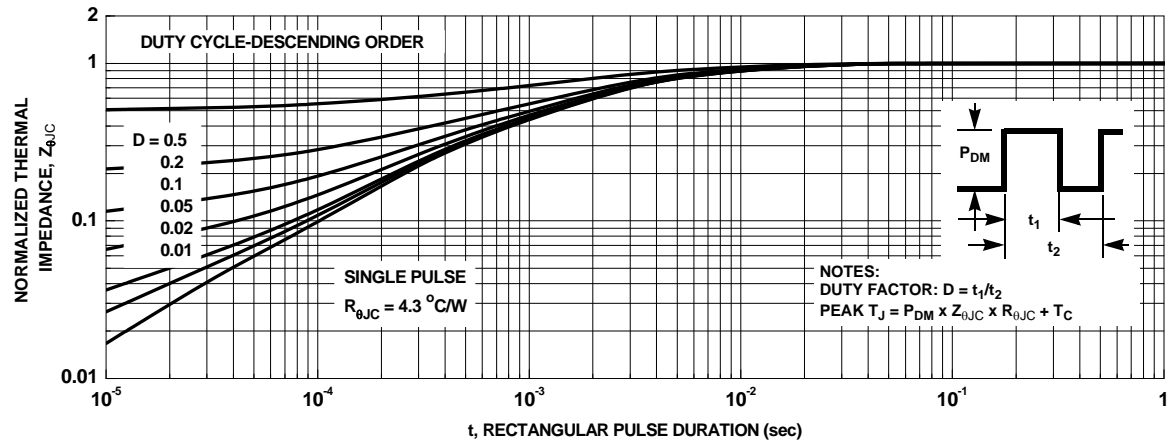
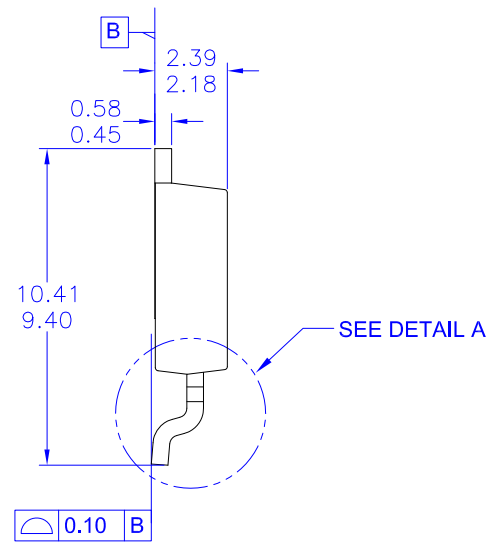
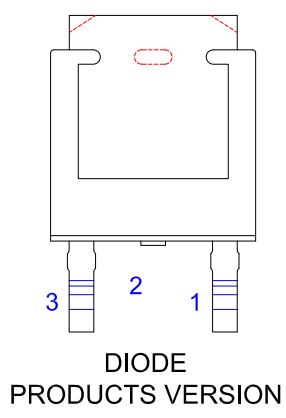
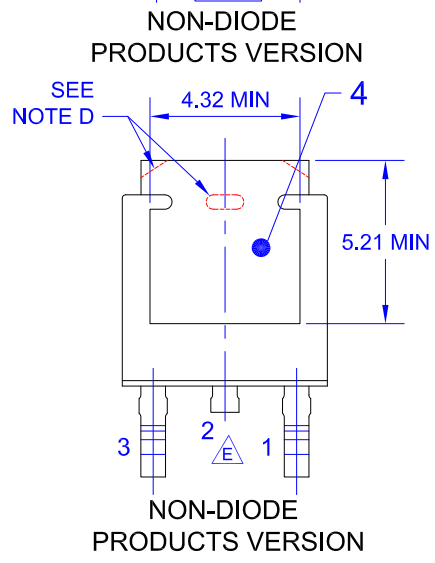
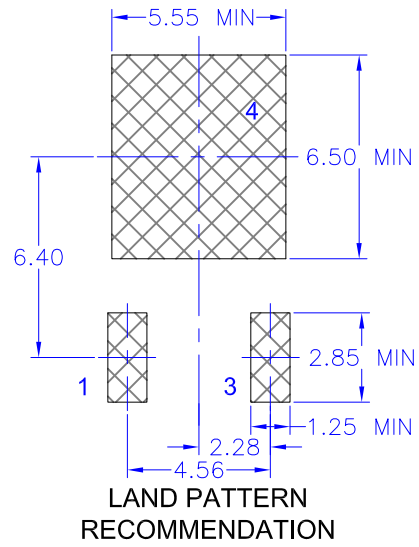
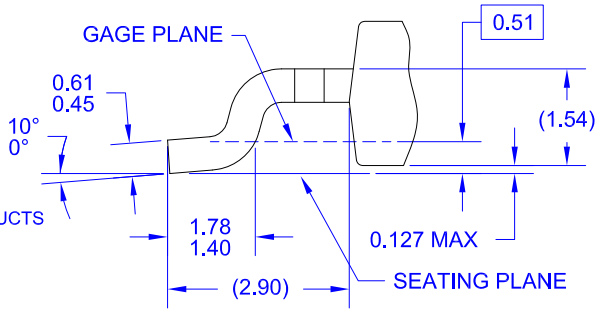


Figure 14. Junction-to-Case Transient Thermal Response Curve



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
 - D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
 - E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS
 - F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.
 - G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
 - H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



DETAIL A
(ROTATED -90°)
SCALE: 12X



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